74AUP1G07

Low-power buffer with open-drain output Rev. 03 — 17 June 2009

Product data sheet

General description

The 74AUP1G07 provides the single non-inverting buffer with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}.

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power buffer with open-drain output

3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP1G07GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AUP1G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP1G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891					

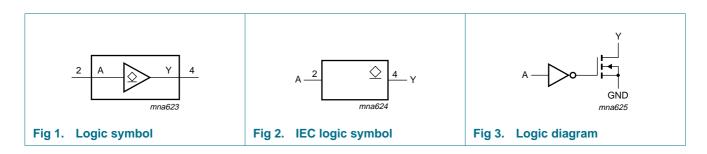
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G07GW	pS
74AUP1G07GM	pS
74AUP1G07GF	pS

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

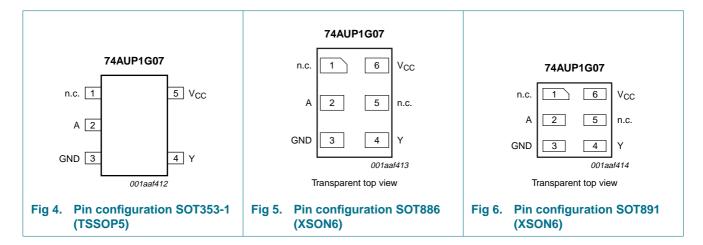
5. Functional diagram



Low-power buffer with open-drain output

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5	XSON6	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V_{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table[1]

Input	Output
A	Υ
L	L
Н	Z

- [1] H = HIGH voltage level;
 - L = LOW voltage level;
 - Z = high-impedance OFF state.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+4.6	V
I_{OK}	output clamping current	V _O < 0 V	-50	-	mA
V_{O}	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I_{O}	output current	$V_O = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
V_{I}	input voltage		0	3.6	V
V_{O}	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	l Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} =	25 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	٧
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	٧
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	٧
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	٧
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	٧
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	٧
l _I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
loz	OFF-state output current	$V_I = V_{IH}$; $V_O = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.1	μΑ
OFF	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
lcc	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
∆l _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	8.0	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.7	-	рF
		output disabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.1	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_O = 1.7 \text{ mA}$; $V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ

75

 $\mu \mathsf{A}$

additional supply current

 ΔI_{CC}

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _{OZ}	OFF-state output current	$V_I = V_{IH}$; $V_O = 0 \ V$ to 3.6 V; $V_{CC} = 0 \ V$ to 3.6 V	-	-	±0.5	μΑ
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
II	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_1 = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ

 $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F		1						
t _{pd}	propagation delay	A to Y; see Figure 7	2]						
		$V_{CC} = 0.8 \text{ V}$	-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.1	4.1	7.5	1.7	9.1	10.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.6	3.0	5.1	1.3	6.1	6.7	ns
		V_{CC} = 1.65 V to 1.95 V	1.6	2.7	4.0	1.2	5.0	5.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.1	2.1	3.2	0.9	4.0	4.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.4	2.2	2.8	1.1	3.3	3.6	ns
C _L = 10	ρF								
t_{pd}	propagation delay	A to Y; see Figure 7	2]						
		$V_{CC} = 0.8 V$	-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.3	3.8	6.1	2.0	7.4	8.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.4	3.6	4.8	1.8	6.1	6.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	2.8	3.8	1.3	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	3.1	4.2	1.6	4.5	5.0	ns
C _L = 15	oF								
t_{pd}	propagation delay	A to Y; see Figure 7	<u>2]</u>						
		$V_{CC} = 0.8 \text{ V}$	-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	4.5	6.8	2.6	8.6	9.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.8	4.4	6.7	2.2	7.8	8.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.4	3.4	4.5	1.9	5.3	5.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	4.0	5.7	1.9	6.1	6.7	ns
C _L = 30									
t_{pd}	propagation delay	A to Y; see Figure 7	<u>2]</u>						
		$V_{CC} = 0.8 V$	-	24.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.8	9.0	15.6	4.3	18.8	20.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.1	6.7	9.4	3.7	11.8	13.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.8	6.8	9.7	3.2	11.0	12.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	3.7	5.2	6.7	3.0	7.1	7.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	3.6	6.4	9.7	2.8	10.4	11.4	ns

Low-power buffer with open-drain output

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C		25 °C	Unit	
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	0.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.7	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.2	-	-	-	-	pF

^[1] All typical values are measured at nominal V_{CC}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

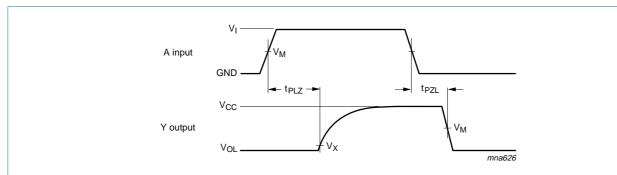
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

 V_{CC} = supply voltage in V;

N = number of inputs switching.

12. Waveforms



Measurement points are given in Table 9.

Logic level: V_{OL} is the typical output voltage drop that occur with the output load.

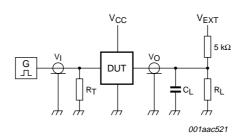
Fig 7. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output			
V _{CC}	V _M	V _M	V_X		
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.1 V		
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V		
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V		

^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

Table 10. Test data

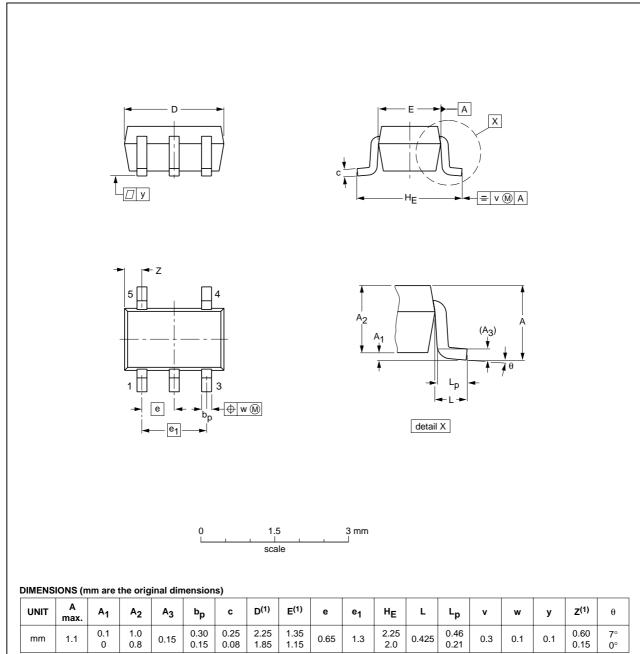
Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

REFERENCES			EUROPEAN	ISSUE DATE	
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	MO-203	SC-88A			00-09-01 03-02-19
	IEC	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 9. Package outline SOT353-1 (TSSOP5)

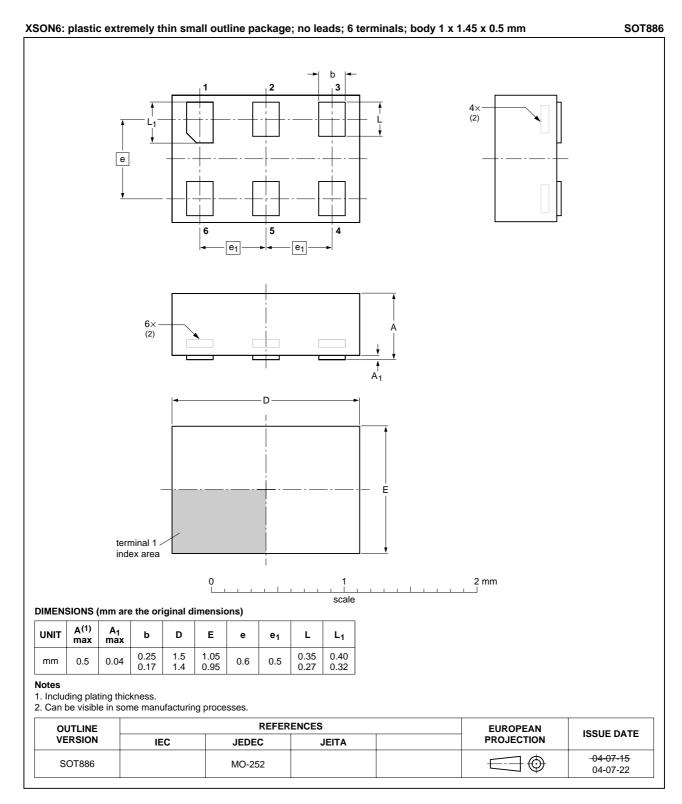


Fig 10. Package outline SOT886 (XSON6)

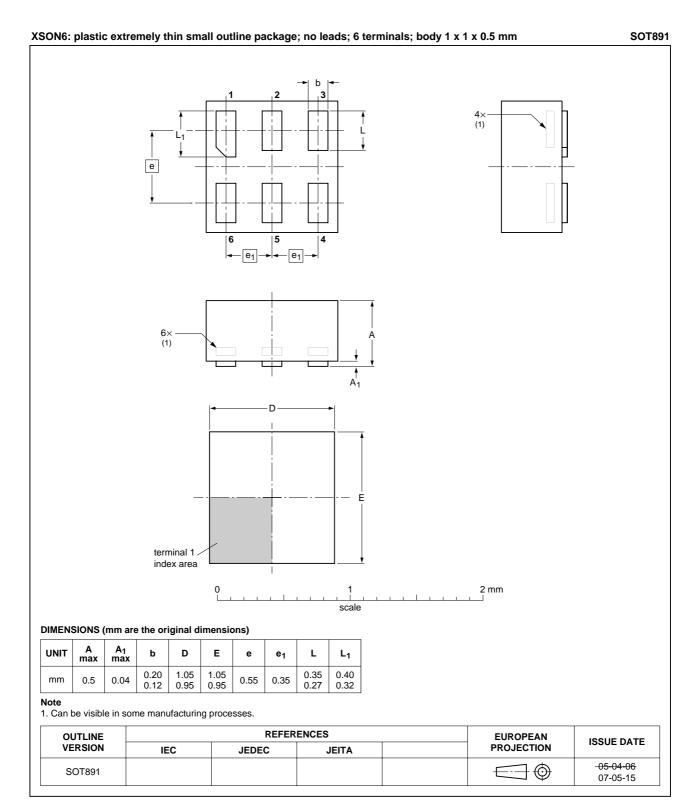


Fig 11. Package outline SOT891 (XSON6)

Low-power buffer with open-drain output

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G07_3	20090617	Product data sheet	-	74AUP1G07_2
Modifications:		ating factor XSON6 has beer formula has been changed.	n changed.	
74AUP1G07_2	20070614	Product data sheet	-	74AUP1G07_1
74AUP1G07_1	20061010	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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